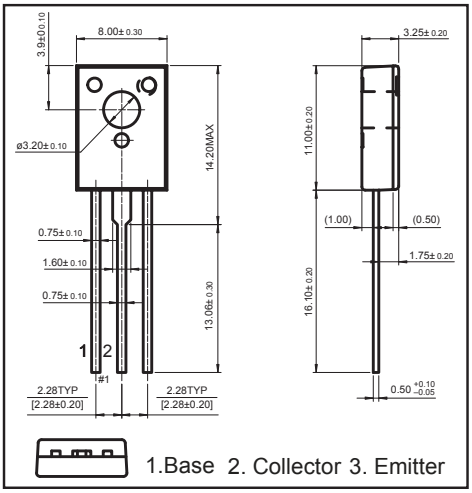
TO-126 Plastic-Encapsulate Transistors

FEATURES

- Low Frequency Power Amplifier
- High Current
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

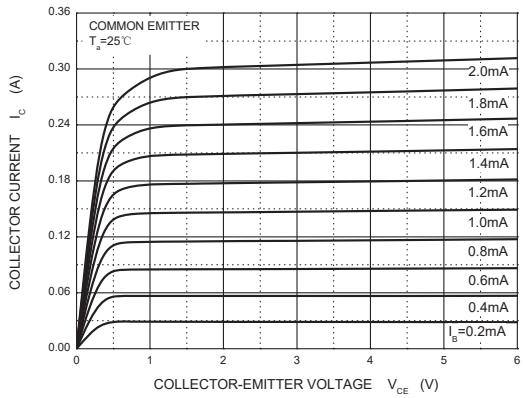
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector- Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	1.5	A
Collector Dissipation	P_C	1	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 ~+150	℃

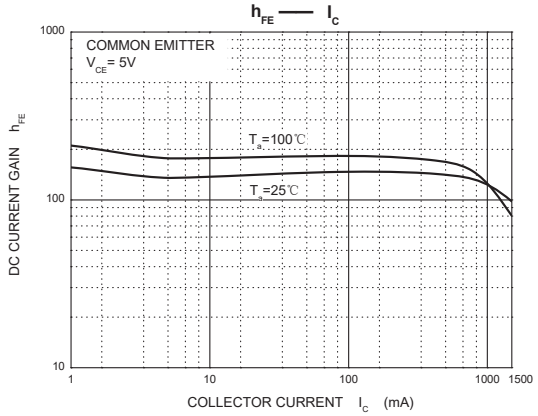
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA, I_B=0	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=160V, I_E=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V, I_C=0			10	μA
DC current gain	$h_{FE(1)}$	V_{CE}=5V, I_C=150mA	60		200	
	$h_{FE(2)}$	V_{CE}=5V, I_C=500mA	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA			1	V
Base-emitter voltage	V_{BE}	V_{CE}=5V, I_C=150mA			1.5	V
Transition frequency	f_T	V_{CE}=5V, I_C=500mA		140		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		14		pF

RATINGS AND CHARACTERISTIC CURVES

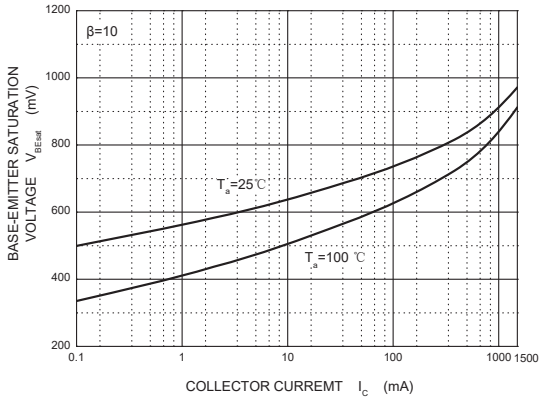
Static Characteristic



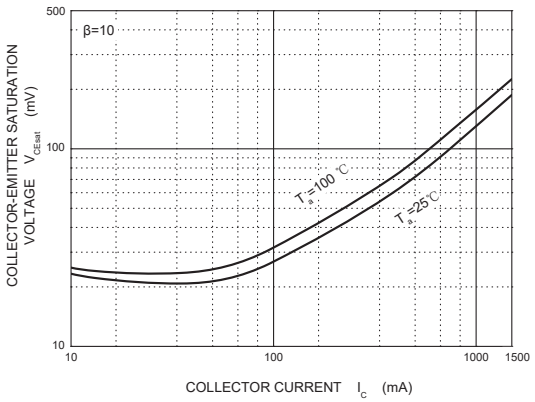
h_{FE} — I_C



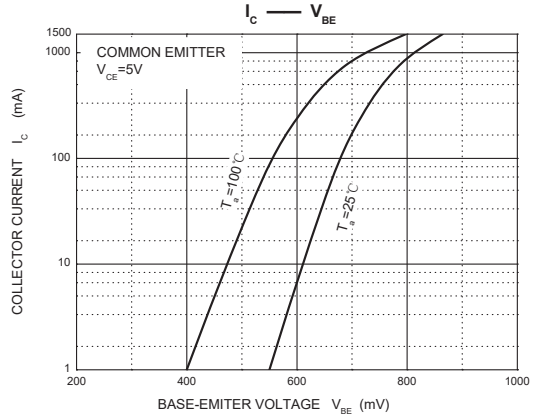
V_{BEsat} — I_c



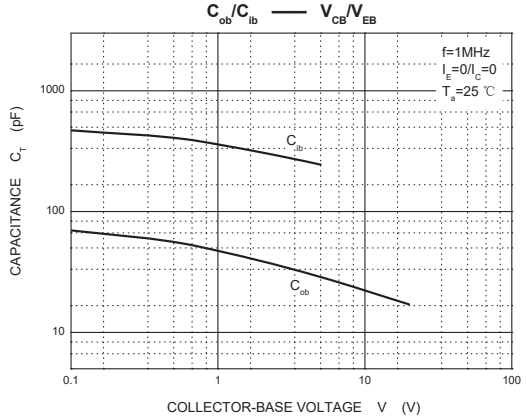
V_{CEsat} — I_C



I_C — V_{BE}



C_{ob}/C_{ib} — V_{CB}/V_{EB}



P_C — T_a